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2A, 200V - 1000V Fast Recovery Surface Mount Rectifier

FEATURES

- AEC-Q101 qualified
- Glass passivated chip junction
- Ideal for automated placement
- Low power loss, high efficiency
- Fast switching for high efficiency
- Low profile package
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Freewheeling
- Snubber
- DC/DC converters
- Automotive application

MECHANICAL DATA

- Case: Thin SMA
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: Indicated by cathode band
- Weight: 0.029g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I _F	2	А	
V _{RRM}	200 - 1000	V	
I _{FSM}	50	А	
T _{J MAX}	150	°C	
Package	Thin SMA		
Configuration	Single die		



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	RS2D	RS2G	RS2J	RS2K	RS2M	UNIT
			ALH	ALH	ALH	ALH	ALH	_
Marking code on the device			RS2DAH	RS2GAH	RS2JAH	RS2KAH	RS2MAH	
Repetitive peak reverse voltage		V_{RRM}	200	400	600	800	1000	V
Reverse voltage, total rms value		V _{R(RMS)}	140	280	420	560	700	V
Forward current		I _F	2					А
Surge peak forward current,	t = 8.3ms		50					А
single half sine-wave superimposed on rated load	t = 1.0ms	I _{FSM}	140					Α
Junction temperature		Τ _J	-55 to +150					°C
Storage temperature		T _{STG}	-55 to +150				°C	



RS2DALH – RS2MALH

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THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance	R _{eJL}	16	°C/W	
Junction-to-ambient thermal resistance	R _{eja}	73	°C/W	
Junction-to-case thermal resistance	R _{eJC}	14	°C/W	

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
		$I_F = 1A, T_J = 25^{\circ}C$		0.93	-	V
	RS2DALH	$I_F = 2A, T_J = 25^{\circ}C$		1.01	1.30	V
	RS2GALH RS2JALH	$I_F = 1A, T_J = 125^{\circ}C$		0.78	-	V
Γ_{orr}		$I_F = 2A, T_J = 125^{\circ}C$	N	0.88	1.02	V
Forward voltage ⁽¹⁾		$I_F = 1A, T_J = 25^{\circ}C$	- V _F	0.98	-	V
	RS2KALH	$I_F = 2A, T_J = 25^{\circ}C$		1.06	1.30	V
	RS2MALH	$I_F = 1A, T_J = 125^{\circ}C$		0.83	-	V
		$I_F = 2A, T_J = 125^{\circ}C$		0.93	1.05	V
Reverse current @ rated V _R ⁽²⁾		$T_J = 25^{\circ}C$		-	1	μA
		T _J = 125°C	– I _R	-	40	μA
	RS2DALH RS2GALH	$I_F = 0.5A, I_R = 1.0A,$ $I_{rr} = 0.25A$	t _{rr}	-	150	ns
Reverse recovery time	RS2JALH			-	250	ns
	RS2KALH RS2MALH			-	500	ns
Junction capacitance	RS2DALH RS2GALH RS2JALH	1MHz, V _R = 4.0V	CJ	11	-	pF
	RS2KALH RS2MALH		-	10	-	pF

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING		
RS2xALH	Thin SMA	14,000 / Tape & Reel		

Notes:

1. "x" defines voltage from 200V(RS2DALH) to 1000V(RS2MALH)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

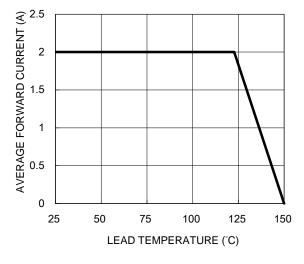


Fig.3 Typical Reverse Characteristics

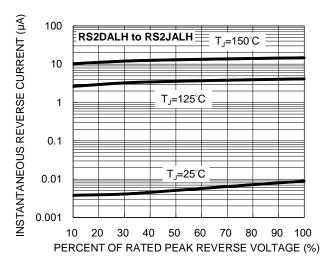
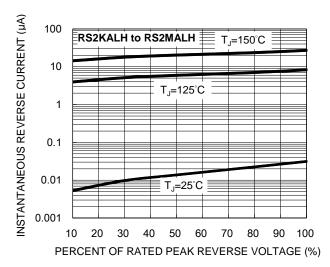
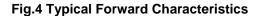


Fig.5 Typical Reverse Characteristics



100 **RS2DALH to RS2JALH RS2KALH to RS2MALH** CAPACITANCE (pF) 10 f=1.0MHz Vsig=50mVp-p 1 100 1 10 **REVERSE VOLTAGE (V)**

Fig.2 Typical Junction Capacitance



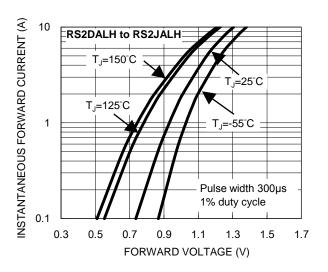
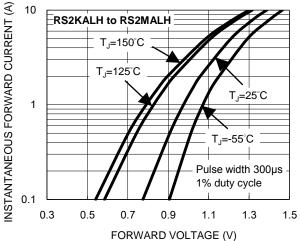


Fig.6 Typical Forward Characteristics



RS2DALH – RS2MALH



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

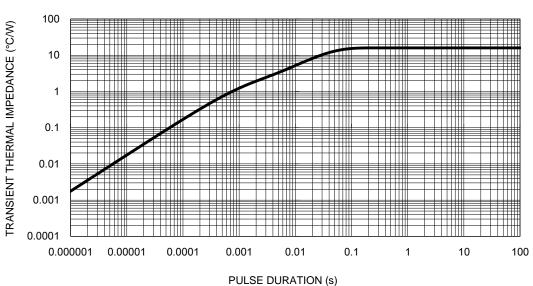


Fig.7 Typical Transient Thermal Impedance

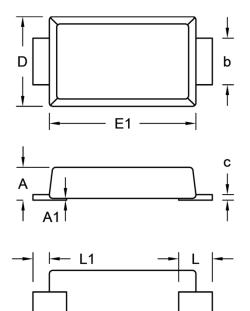


RS2DALH – RS2MALH

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PACKAGE OUTLINE DIMENSIONS

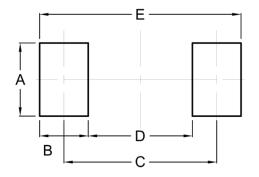




	DIM.		Unit (inch)	
	Min.	Max.	Min.	Max.
A	0.90	1.00	0.035	0.039
A1	0.00	0.10	0.000	0.004
b	1.25	1.45	0.049	0.057
с	0.10	0.22	0.004	0.009
D	2.50	2.70	0.098	0.106
E	5.05	5.35	0.199	0.211
E1	4.15	4.35	0.163	0.171
L	0.75	1.20	0.030	0.047
L1	0.30	0.60	0.012	0.024

SUGGESTED PAD LAYOUT

- E -



Symbol	Unit (mm)	Unit (inch)
А	2.10	0.083
В	1.40	0.055
С	4.40	0.173
D	3.00	0.118
E	5.80	0.228

MARKING DIAGRAM



P/N	= Marking Code
YW	= Date Code
F	= Factory Code



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